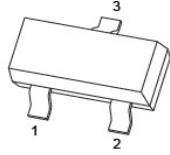
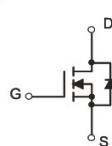
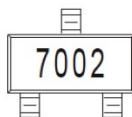


V(BR)DSS	RDS(ON)MAX	ID
60V	5Ω@10V 7Ω@5V	115mA

SOT-23

1. GATE
2. SOURCE
3. DRAIN


Equivalent Circuit

MARKING

特征 Features

- High density cell design for low $R_{DS(ON)}$.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.
- Load Switch for Portable Devices.
- DC/DC Converter.

机械数据 Mechanical Data

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package.
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0.
- 安装位置: 任意 Mounting Position: Any.

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

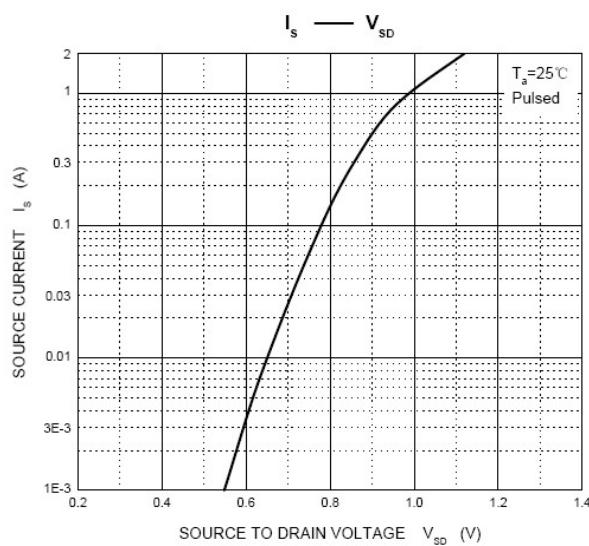
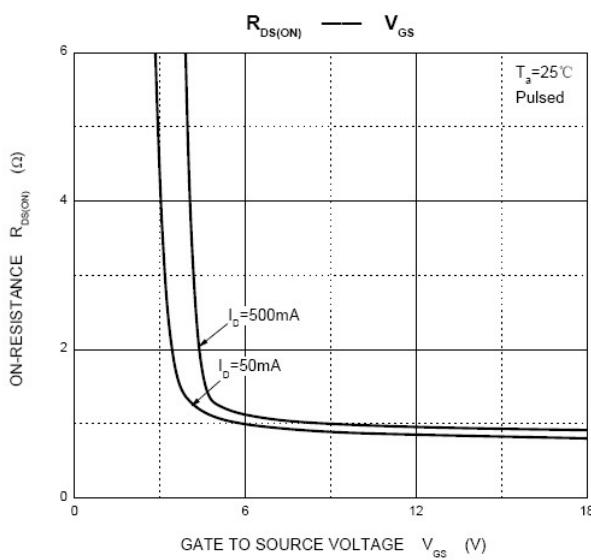
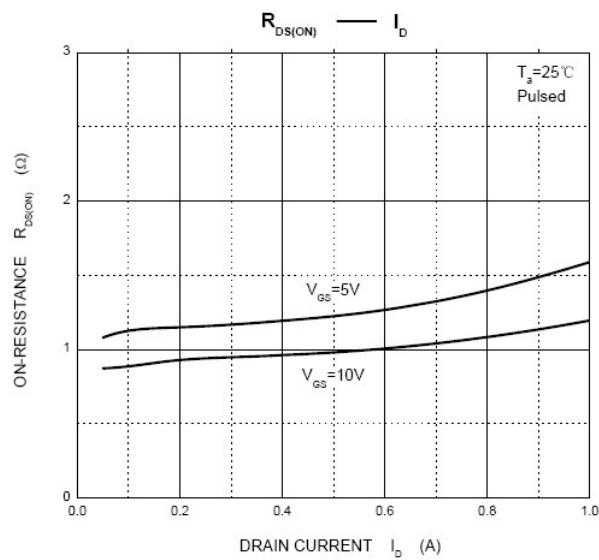
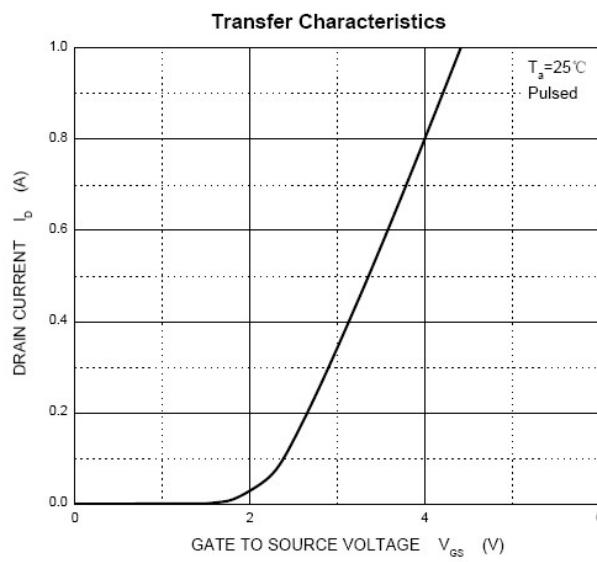
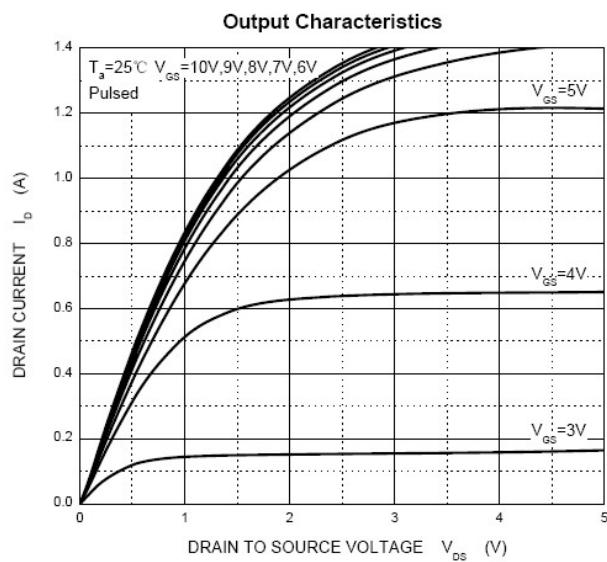
参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	115	mA
Power Dissipation	P_D	225	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-50~+150	°C
Thermal Resistance From Junction to Ambient	$R_{\theta JA}$	556	°C/W

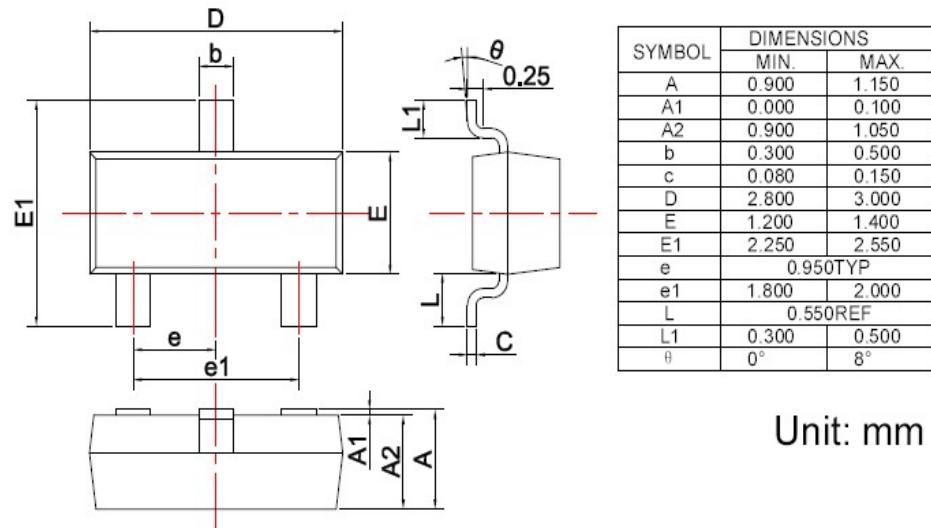
电特性 (TA = 25°C 除非另有规定)

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

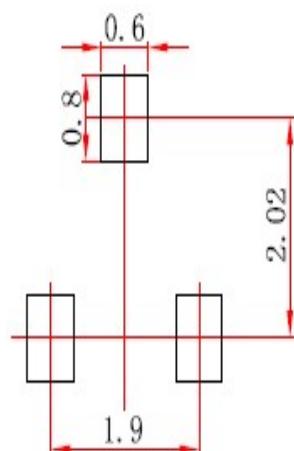
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	60		V
Gate-Threshold voltage	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	2.5	V
Gate-body Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$		± 10	μA
Zero Gate Voltage Drain current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$		80	nA
On-state Drain current	$I_D(ON)$	$V_{GS}=10V, V_{DS}=7V$	500		mA
Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=500mA$ $V_{GS}=5V, I_C=50mA$		5 7	Ω
Forward Trans conductance	g_{fs}	$V_{DS}=10V, I_D=200mA$	80		ms
Drain-source on-voltage	$V_{DS(ON)}$	$V_{GS}=10V, I_D=500mA$ $V_{GS}=5V, I_D=50mA$		3.75 0.375	V
Diode Forward voltage	V_{SD}	$I_S=115mA, V_{GS}=0V$	0.55	1.20	V
Input capacitance*	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$		50	pF
Output capacitance*	C_{oss}			25	
Reverse Transfer capacitance*	C_{rss}			5	
SWITCHING TIME					
Turn-on Time*	$t_{d(on)}$	$V_{DD}=25V, R_L=50\Omega, I_D=500mA,$ $V_{GEN}=10V, R_G=25\Omega$		20	ns
Turn-off Time*	$t_{d(off)}$			40	

* These parameters have on way to verify.

Typical characteristics


SOT-23 PACKAGE OUTLINE Plastic surface mounted package

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs


Note:

1. Controlling dimension: In millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

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